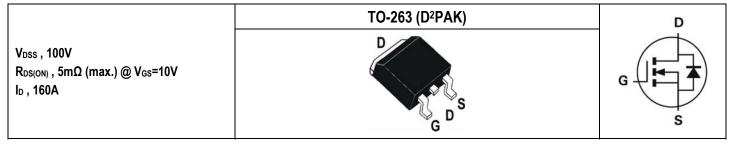


SG100N05G

100V N-Channel Power MOSFET



Description	Features
The SG100N05G uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	Low Miller Charge
	Pb-free lead plating; RoHS compliant
	Applications
	Motor / Body Load Control
	Load Switch
	Solenoid and Motor Control
	 DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG100N05G	Halogen-Free	TO-263 (D ² PAK)	G	Tape & Reel	800

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parame	ter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous	Tc=25°C	1-	160	Α
Drain Current-Continuous	Tc=70°C	lD ID	135	А
Drain Current-Pulsed Note 1	·	I _{DM}	620	Α
T _A =25°C			14.5	А
Drain Current-Continuous	T _A =70°C	lD	12	А
Avalanche Current, L=0.5mH		I _{AS}	40	А
Avalanche Energy, L=0.5mH		Eas	400	mJ
	Tc=25°C		300	W
Maximum Dawar Dissinction	T _C =70°C	D	210	W
Maximum Power Dissipation	T _A =25°C		2.4	W
	T _A =70°C		1.68	W
Storage Temperature Range		T _{STG}	-55 to +175	°C
Operating Junction Temperature Range		TJ	-55 to +175	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	Steady State	-	-	62.5	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	0.5	°C/W



SG100N05G

100V N-Channel Power MOSFET

Electrical Characteristics (T_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	2	3	4	V
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =10V, I _{DS} =30A	-	-	5	mΩ

DYNAMIC CHARACTERISTICS Conditions Parameter Symbol Min. Тур. Max. Unit -Input Capacitance C_{iss} 8931 -**Output Capacitance** C_{oss} _ 595 pF V_{DS}=30V, V_{GS}=0V, f=1MHz _ 239 **Reverse Transfer Capacitance** C_{rss} --

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	25	-	
Rise Time	tr	V _{DD} =30V, I _D =30A,	-	40	-	
Turn-Off Delay Time	T _{d(off)}	V_{GEN} =10 V , R_{G} =3.3 Ω	-	85	-	ns
Fall Time	t _f		-	45	-	
Total Gate Charge at 10V	Qg		-	160	-	
Gate to Source Gate Charge	Q_gs	V _{DS} =30V, V _{GS} =10V, I _{DS} =30A	-	35	-	nC
Gate to Drain "Miller" Charge	Q_{gd}	105-307	-	40	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{DS} =30A	-	-	1.3	V	
Body Diode Reverse Recovery Time	trr		-	120	-	ns	
Body Diode Reverse Recovery Charge	Qrr	l⊧=30A, dl/dt=100A/µs	-	160	-	nC	

Notes:

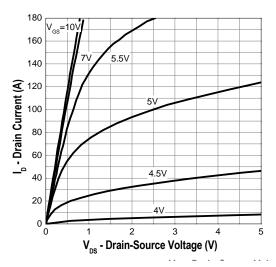
1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

 R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 in still air.

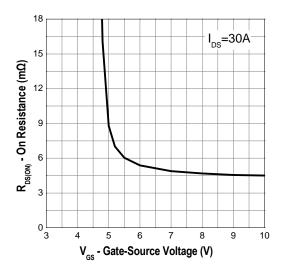


Typical Operating Characteristics

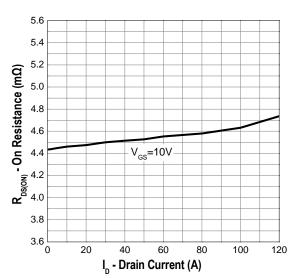
Output Characteristics



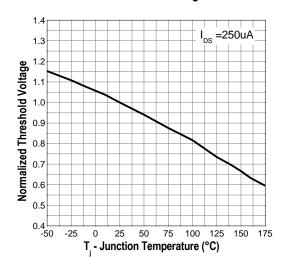
Gate-Source On Resistance



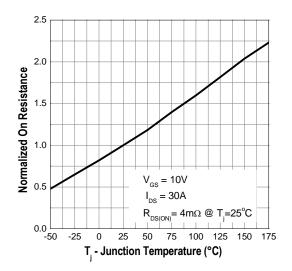
Drain-Source On Resistance

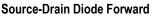


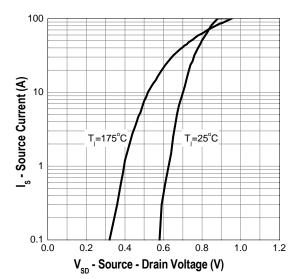
Gate Threshold Voltage



Drain-Source On Resistance





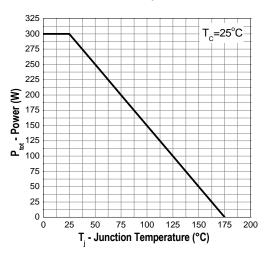


SG100N05G 100V N-Channel Power MOSFET

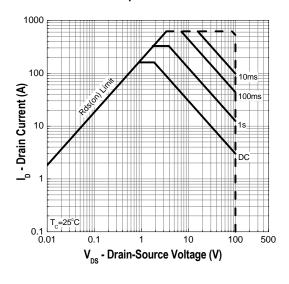


Typical Operating Characteristics (Cont.)

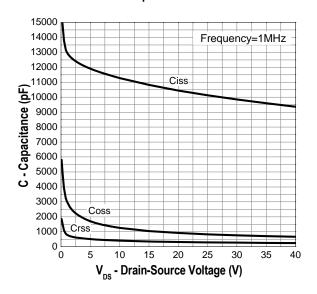
Power Dissipation

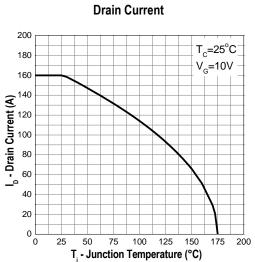


Safe Operation Area



Capacitance

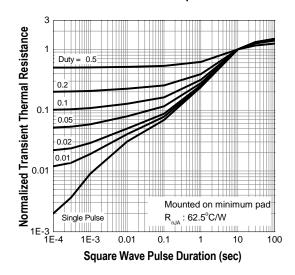




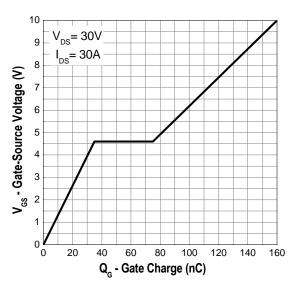
SG100N05G

100V N-Channel Power MOSFET

Transient Thermal Impedance

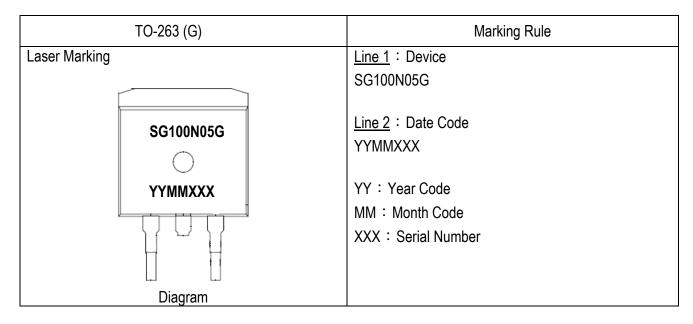








Marking Information

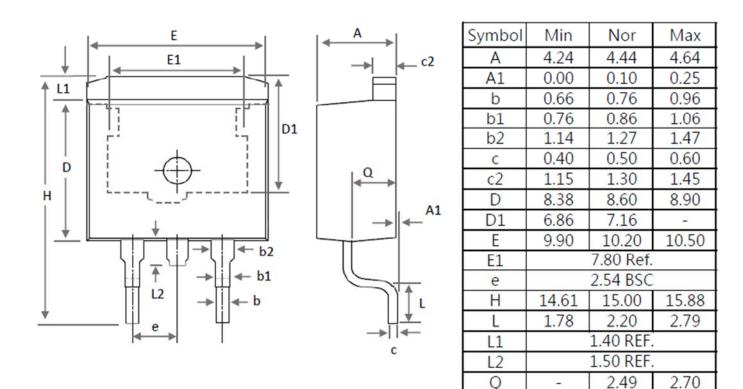




Package of Dimension

SG100N05G 100V N-Channel Power MOSFET

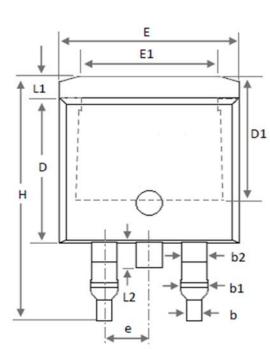
TO-263S

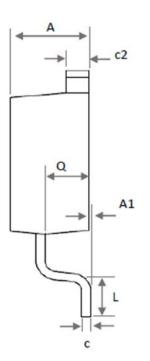




Package of Dimension

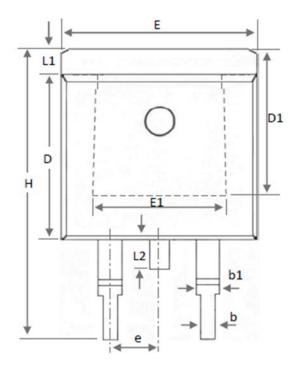
G-TYPE





Symbol	Min	Nor	Max
Α	4.24	4.51	4.77
A1	0.00	0.13	0.25
b	0.70	0.83	0.96
b1	1.17	1.46	1.75
b2	1.20	1.45	1.70
С	0.30	0.45	0.60
c2	1.15	1.29	1.42
D	8.50	8.76	9.02
D1	6.60	7.13	7.65
E	9.86	10.11	10.36
E1	6.89	7.39	7.89
e		2.54 BSC	
Н	14.61	15.25	15.88
L	1.78	2.29	2.79
L1	1.07	1.27	1.47
L2	1.40	1.55	1.70
Q	2.30	2.60	2.89

H-TYPE



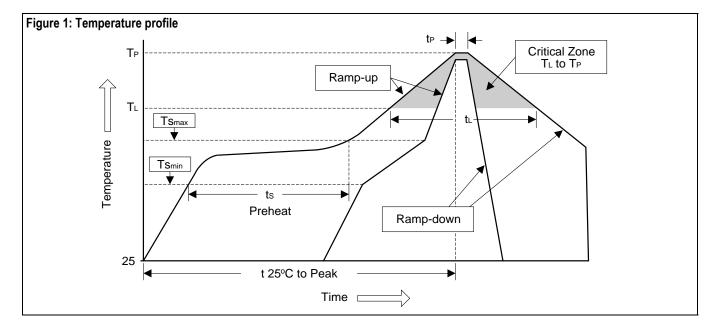
SG100N05G 100V N-Channel Power MOSFET

TO-263



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate $(T_L \text{ to } T_P)$	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t _P)		20 10 40 360
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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